

Peter Lagov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

22 papers	203 citations	8 h-index	14 g-index
26 ext. papers	255 ext. citations	1.9 avg, IF	2.67 L-index

#	Paper	IF	Citations
22	Laser ion source for semiconductor applications. <i>Journal of Physics: Conference Series</i> , 2022 , 2244, 0120963	0.3	0
21	1 GeV proton damage in EgGa_2O_3 . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
20	Crystal orientation dependence of deep level spectra in proton irradiated bulk EgGa_2O_3 . <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
19	Effect of Electron Irradiation on the Optical Properties of Gadolinium-Aluminum-Gallium Garnet Crystals. <i>Journal of Surface Investigation</i> , 2021 , 15, 1259-1263	0.5	0
18	Comparison of the Helium Porosity Parameters in Vanadium Alloy TEM Samples Prepared by Various Techniques. <i>Russian Metallurgy (Metally)</i> , 2020 , 2020, 206-211	0.5	
17	Nanosilicon stabilized with ligands: Effect of high-energy electron beam on luminescent properties. <i>Surface and Interface Analysis</i> , 2020 , 52, 957-961	1.5	4
16	Pulsed fast reactor neutron irradiation effects in Si doped n-type EgGa_2O_3 . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
15	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 445111	3	3
14	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. <i>Journal of Applied Physics</i> , 2019 , 126, 125708	2.5	14
13	Features of Gas Porosity Formation Along Helium Ion Trajectories in Vanadium Alloys. <i>Atomic Energy</i> , 2019 , 126, 46-51	0.4	
12	Detection of Unreliable Superluminescent Diode Chips Using Gamma-Irradiation. <i>Lecture Notes in Mechanical Engineering</i> , 2019 , 309-317	0.4	
11	Development of Gas Porosity along the Ion Range in Vanadium Alloys during Sequential Helium and Hydrogen Ion Irradiation. <i>Russian Metallurgy (Metally)</i> , 2019 , 2019, 1161-1166	0.5	1
10	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P323-P328	2	9
9	Hole traps and persistent photocapacitance in proton irradiated EgGa_2O_3 films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
8	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated EgGa_2O_3 . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
7	Deep Electron and Hole Traps in Electron-Irradiated Green GaN/InGaN Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q127-Q131	2	9
6	Proton-irradiation technology for high-frequency high-current silicon welding diode manufacturing. <i>Journal of Physics: Conference Series</i> , 2017 , 830, 012152	0.3	1

5	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , 2017 , 122, 115704	2.5	19
4	Electron irradiation of near-UV GaN/InGaN light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700372	1.6	10
3	Accelerator-based electron beam technologies for modification of bipolar semiconductor devices. <i>Journal of Physics: Conference Series</i> , 2016 , 747, 012085	0.3	8
2	Magnetic Buncher Accelerator for Radiation Hardness Research and Pulse Detector Characterization 2015 ,		5
1	Particularities of Vanadium Microstructure Development During Irradiation by 7.5 MeV Ni ²⁺ Ions at 650°C. <i>Atomic Energy</i> , 2015 , 118, 400-404	0.4	2